

MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

MIC5225-x.xYM5-TR-MS

产品手册

概述

MIC5225-x.xYM5-TR-MS 系列是一组低压差 (LDO)转换器, 具有 2.8V 至 20V 宽电压输入范围、低压差、低功耗和小型化封装的等特性, 输出电压范围为 3.0-5.0V。

MIC5225-x.xYM5-TR-MS 低至 1.8uA 低静态电流特性,电路也带有 CE 使能控制端口,可使电路进入休眠状态。特别适合用于电池供电、长时间待机系统设备应用,能帮助降低系统设备的待机功耗,有效延长待机时间和电池使用寿命。

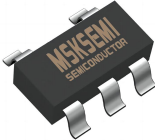
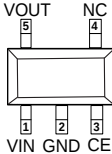
主要特点

- 输入输出电压差低
- 温度漂移系数小
- 耐压 20V
- 工作静态电流 1.8μA, 最大 4μA
- 休眠静态电流最大 0.2μA
- 输出电压精度: ±2%
- 输出过载保护
- 带有 CE 使能控制端口
- 工作温度 - 20°C ~ + 85°C

典型应用

- 手持式、电池供电设备
- 通信设备
- 音频、视频设备
- 低功耗微处理器
- 笔记本电脑、掌上型电脑和 PDA
- 车载导航系统
- 工业控制
- 智能家居

封装脚位信息

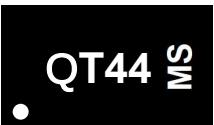
SOT-23-5	封装脚位图
	

引脚功能描述

序号	符号	功能描述
1	VIN	输入端
2	VSS	地端
3	CE	使能端
4	NC	悬空
5	VOUT	输出端

管体标记

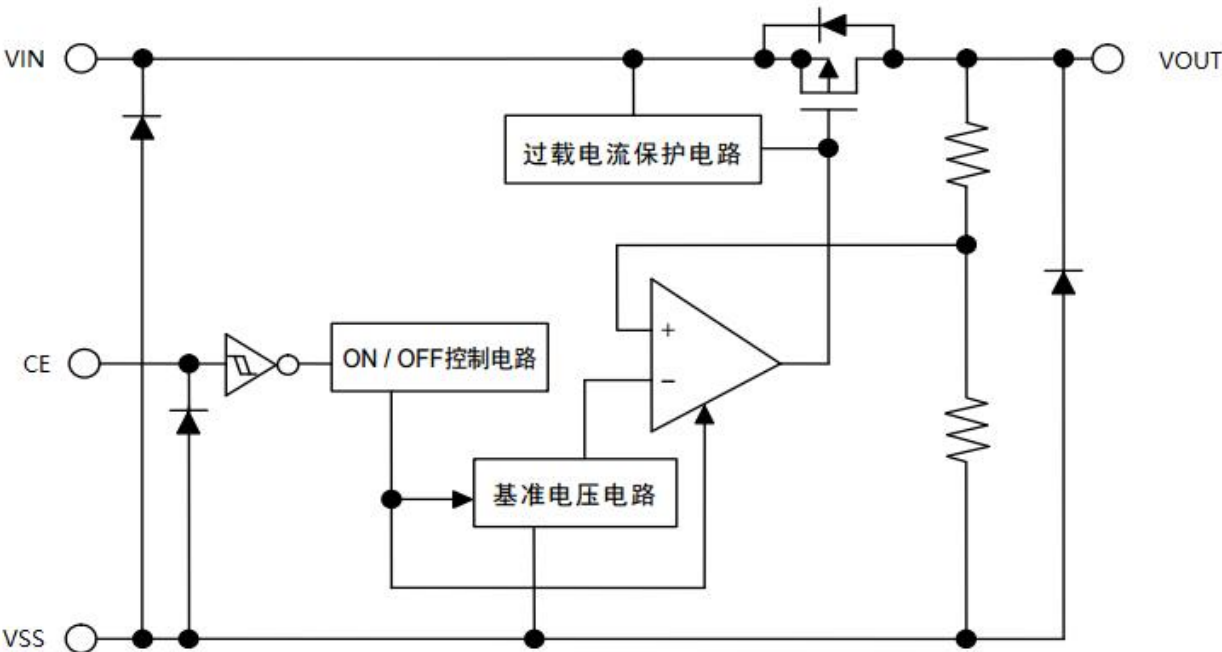
MIC5225-3.0YM5-TR-MS	MIC5225-3.3YM5-TR-MS	MIC5225-3.6YM5-TR-MS
		

MIC5225-4.0YM5-TR-MS	MIC5225-4.4YM5-TR-MS	MIC5225-5.0YM5-TR-MS
		

订货信息

型号	输出电压	容差	封装类型	最小包装
MIC5225-3.0YM5-TR-MS	3.0V	2%	SOT-23-5	3000PCS
MIC5225-3.3YM5-TR-MS	3.3V			
MIC5225-3.6YM5-TR-MS	3.6V			
MIC5225-4.0YM5-TR-MS	4.0V			
MIC5225-4.4YM5-TR-MS	4.4V			
MIC5225-5.0YM5-TR-MS	5.0V			

电路方框图



最大额定值 (无特别说明情况下, TA=25℃)

参数说明	符号	数值范围	单位
输入极限电压	V_{IN}	-0.3 ~ +26	V
使能口极限电压	V_{CE}	-0.3 ~ +26	V
输出极限电流	I_{out}	600	mA
贮存温度	T_{STG}	-50 ~ +125	℃
工作温度	T_A	-20 ~ +85	℃
结温 ⁽¹⁾	T_J	150	℃

注：超最大额定值应用可能会对器件造成永久性损伤。

散热信息

参数说明	符号	数值范围	单位
功耗	P_D	200	mW

电气参数 (无特别说明情况下, TA=25℃, CIN=COU=1uF)

参数说明	符号	测试条件	最小值	典型值	最大值	单位
输入电压	V _{IN}		3.0		20	V
输出电压	V _{OUT}		3.0		5.0	V
输出电压精度		I _{OUT} =1mA	-2		+2	%
输出电流	I _{OUT}	V _{IN} =V _{OUT} +2.0V	—	150	—	mA
负载调整率	△V _{OUT}	V _{IN} =V _{OUT} +2.0V 1mA≤I _{OUT} ≤150mA	—	15	—	mV
线性调整率	△V _{OUT} / V _{OUT} * △V _{IN}	V _{OUT} +1.0V≤V _{IN} ≤20V I _{OUT} =10mA	—	0.015	0.2	%/V
低压差	V _{DIF} ^①	I _{OUT} =100mA,V _{OUT} =3.3V	—	200	—	mV
静态电流	I _{SS}	V _{CE} =V _{IN}	—	1.8	4	μA
休眠电流	I _{STANDBY}	V _{CE} =V _{SS}			0.2	μA
使能高电平	V _{CEH}	V _{IN} =V _{OUT} +2.0V	1.7		20	V
使能低电平	V _{CEL}	V _{IN} =V _{OUT} +2.0V	0		0.3	V
短路电流	I _{SHORT}	V _{IN} =V _{OUT} +2.0V	—	400	—	mA
温度系数	△V _{OUT} / △T _A *V _{OUT}	V _{IN} =V _{OUT} +2.0V I _{OUT} =10mA -40℃≤T _A ≤125℃	—	±100	—	ppm/℃
输出有源放电电阻	R _{DIS} ^②	V _{CE} <0.5V		300		Ω

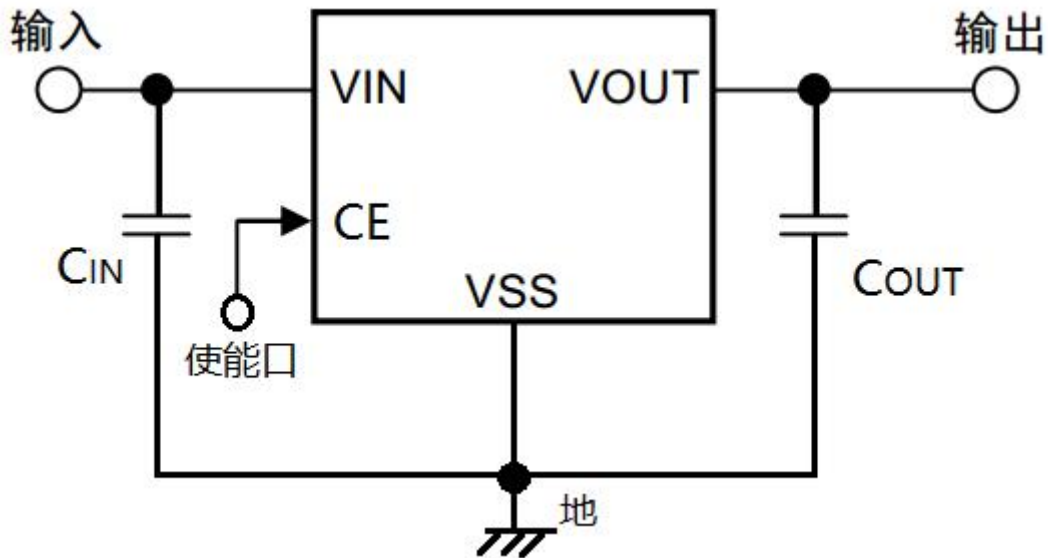
注:

- 1.当V_{IN}=V_{OUT}+2.0V, 固定负载条件下使输出电压下降2%, 此时输入电压和输出电压的差值为低压 差值V_{DIF}。
- 2.输出有源放电电阻R_{DIS}, 随着VIN 电压增大而降低。

应用说明

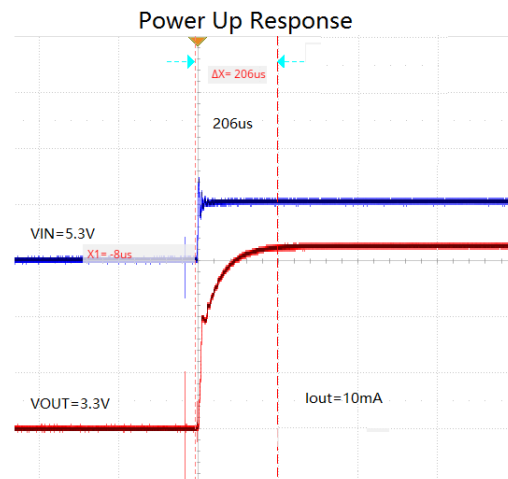
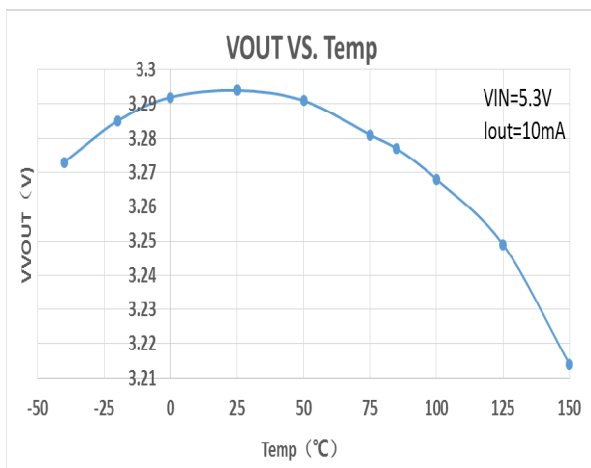
- 1、应用时尽量将电容接到VIN 和VOUT 脚位附近。
- 2、电路内部使用了相位补偿电路和利用输出电容的ESR 来补偿。所以输出到地一定要接大于或者 等于 $1\mu\text{F}$ 的电容器。
- 3、注意输入输出电压、负载电流的使用条件，避免IC 内部的功耗超出封装允许的最大功耗值。

应用电路



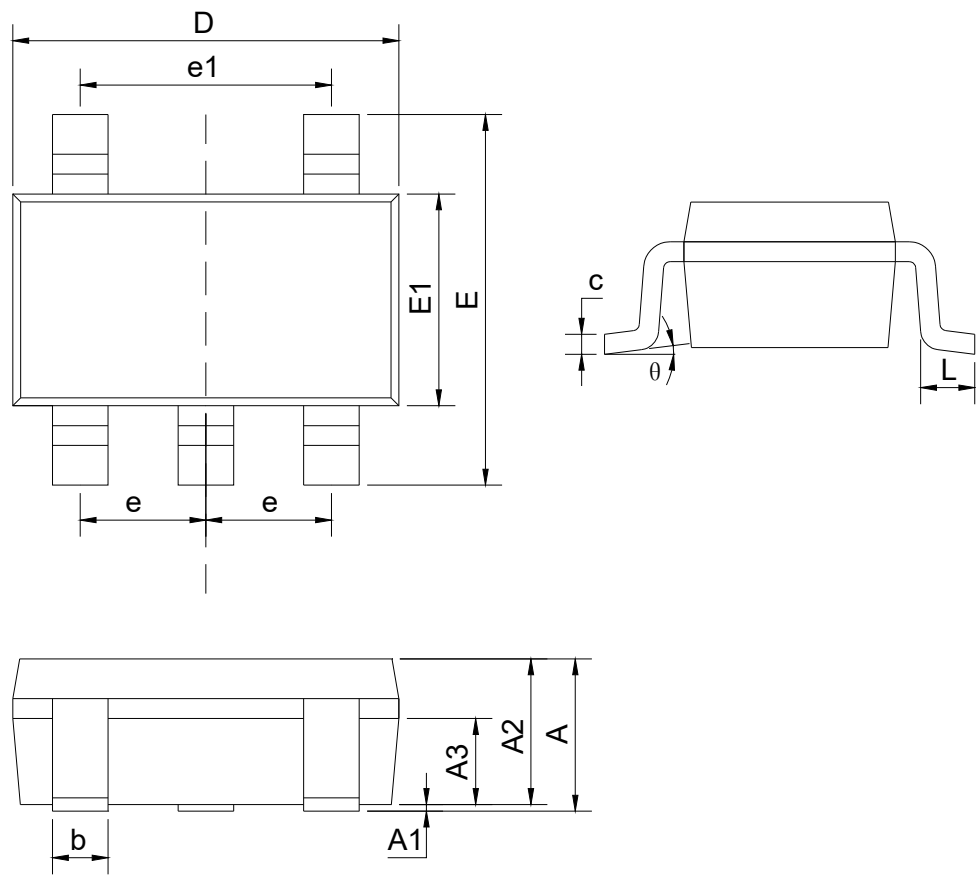
1. C_{IN} 用于稳定输入电容
2. C_{OUT} 可以使用的大于或等于 $1\mu\text{F}$ 的陶瓷电容

典型的性能曲线



封装外形图和尺寸

SOT-23-5



SYMBOL	mm	
	min	max
A		1.35
A1	0.04	0.15
A2	1.00	1.20
A3	0.55	0.75
b	0.38	0.48
c	0.10	0.25
D	2.72	3.12
E	2.60	3.00
E1	1.40	1.80
e	0.95BSC	
e1	1.90BSC	
L	0.30	0.60
θ	0	8°

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